



GVGR-S11SD

- PN-type Photodiode
- Indium Gallium Nitride Based Material
- 295 – 490 nm
- Photovoltaic Operation Mode
- SMD 3528, 3.15 x 2.80 x 1.90 mm



Description

GVGR-S11SD is a Photodiode working in the spectral range of 295 – 490 nm. It contains an Indium Gallium Nitride based chip die, housed into SMD 3528 package, is a great solution, as example for blue LED monitoring, UV curing or UV LED monitoring.

Absolute Maximum Ratings

Parameter	Symbol	Values	Unit
Reverse Voltage	V_R	5	V
Forward Current	I_{OP}	1	mA
Operating Temperature	T_{CASE}	-30 – +85	°C
Storage Temperature	T_{STG}	-40 – +90	°C
Soldering Temperature *	T_{SLD}	260	°C

* must be completed within 10 seconds

Electro-Optical Characteristics

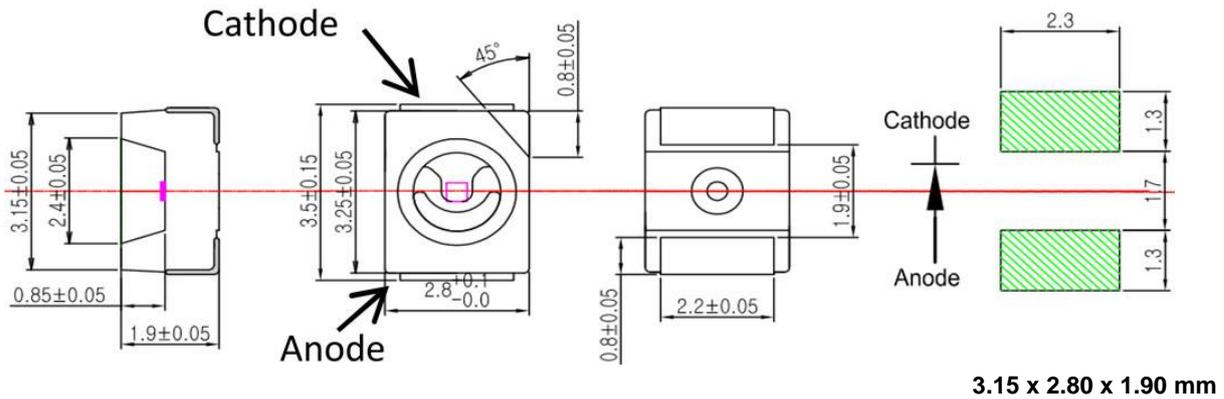
$T_{CASE} = 25^{\circ}C$

Parameter	Symbol	Values	Unit
Dark Current ($V_R=0.1V$)	I_D	max. 1	nA
Photo Current (LED 405nm, 1mW/cm ²)	I_{PH}	typ. 44	nA
Responsivity (405nm, $V_R=0.1V$)	R	typ. 0.07	A/W
Spectral Detection Range	λ	295 – 490	nm
Active Area	A	0.0162	mm ²



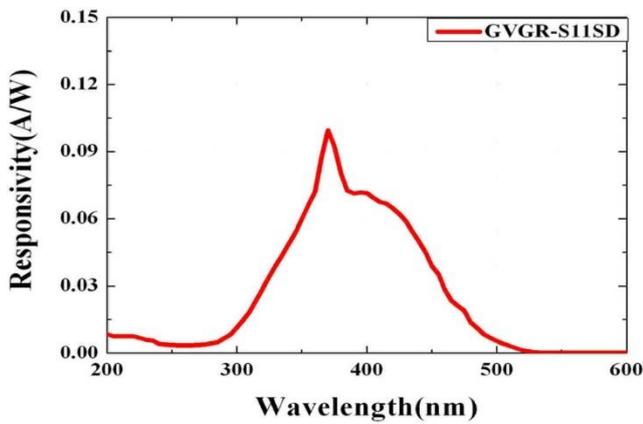
Outline Dimensions

GVGR-S11SD

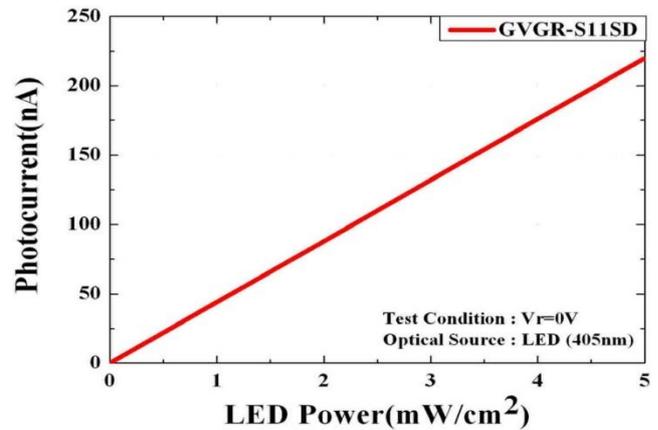


Typical Performance Curves

Relative Responsivity



Output Voltage vs. UV Power



Caution

ESD can damage the device hence please avoid ESD.